

Hopping conductivity in the quantum Hall effect – revival of universal scaling

F. Hohls,^{1,*} U. Zeitler,¹ and R. J. Haug¹

¹*Institut für Festkörperphysik, Universität Hannover, Appelstr. 2, 30167 Hannover, Germany*

We have measured the temperature dependence of the conductivity σ_{xx} of a two-dimensional electron system deep into the localized regime of the quantum Hall plateau transition. Using variable-range hopping theory we are able to extract directly the localization length ξ from this experiment. We use our results to study the scaling behavior of ξ as a function of the filling factor distance $|\delta\nu|$ to the critical point of the transition. We find for all samples a power-law behavior $\xi \propto |\delta\nu|^{-\gamma}$ with a universal scaling exponent $\gamma = 2.3$ as proposed theoretically.

PACS numbers: 73.40.Hm, 71.23.An, 72.20.My, 71.30.+h

The prominent feature of the quantum Hall effect (QHE) is the emergence of quantized plateaus in the Hall resistance of a two-dimensional electron system (2DES) reflecting the localization of states at the Fermi edge. A deeper understanding of this fascinating phenomenon is gained from regarding the transition region between adjacent QHE plateaus [1, 2]. In this regime the dissipative transport is governed by the delocalized states in the vicinity of the Landau level center. The degree of localization is expressed by the localization length ξ denoting the typical extension of the electron wave function. For any sample with a finite size L theory predicts the conductivity tensor in the plateau transition to follow a scaling function $f(L/\xi)$ with a diverging localization length $\xi = |\delta\nu|^{-\gamma}$ [3] where $\delta\nu = \nu - \nu_c$ denotes the filling factor distance to the critical point ν_c of the transition. The critical exponent $\gamma = 2.3$ was predicted to be universal, its value determined numerically [4] and validated by variation of the sample size [5]. Experimentally the scaling of the conductivity near the critical point was verified with great success for different samples by temperature, current, and frequency dependent measurements of the transition width [6, 7, 8]. These new parameters introduce effective lengths $L_T \propto T^{p/2}$, $L_I \propto I^{p/(2+p)}$, and $L_f \propto f^{1/z}$ and thereby add additional exponents z and p . These effective lengths replace the physical sample size L in the scaling functions $f(L/\xi)$. Recent experiments extended the focus to the transition from the quantum Hall state to the Hall insulator [9, 10, 11]. In these investigations striking similarities to the scaling behavior in the transition between different QH states were observed [12] hinting to the same universality class for both types of transitions [13, 14].

In spite of the great success of scaling theory in the QHE there are still some experiments not fitting into the picture of universality. Non-universal exponents were observed in the dependence of the transition width on temperature [15], current [16] and frequency [17]. Other experiments seem to contradict scaling theory at all, both

for the Hall plateau-insulator transition [18] and the transition between QHE plateaus [19, 20].

However, before making conclusions on a general failure of scaling theory it has to be considered that nearly all experiments *do not* measure the localization length ξ directly. Therefore an assumption about the functional form and exponents z and p of the effective length $L_{\text{eff}}(T, I, f)$ has to be made. The non-universal scaling exponents deduced from investigating the QHE transition width as a function of T , I and f then only reflect non-universal exponents p and z in L_{eff} . Additionally, the measurements mostly focus on the region close to critical points, where ξ becomes larger than L_{eff} . In this regime, however, the mechanism of electronic transport at nonzero temperature or frequency is not thoroughly understood. Addressing this problem Shimshoni found in a recent theoretical work for the Hall plateau-insulator transition that for $T > 0$ quantum transport occurs only at some distance to the critical point, namely in the regime of hopping conductivity [21]. Therefore, any lack of universal width scaling with T or f does not necessarily allow to draw conclusions on the behavior of ξ .

In order to avoid such complications, we follow a different approach to scaling. We directly evaluate the localization length in the well understood regime of variable-range hopping (VRH) conductivity [22]. We have recently shown this method to be reliable for frequency dependent measurements [23]. VRH dominates the conductivity at low temperatures, when the localization length becomes much smaller than the effective temperature length L_T . In the QHE regime the VRH conductivity is given as [22, 24, 25]

$$\sigma_{xx}(T) = \sigma_0 \exp\left(-\sqrt{T_0/T}\right), \quad k_B T_0 = C \frac{e^2}{4\pi\epsilon\epsilon_0\xi}, \quad (1)$$

with a temperature dependent prefactor $\sigma_0 \propto 1/T$. The characteristic temperature T_0 is determined by the Coulomb energy at a length scale given by the localization length ξ , the dimensionless constant C being in the

Sample	doping	n_e 10^{15} m^{-2}	μ_e m^2/Vs	ν_c	κ
S1	δ -Be	2.1	2	1.29	0.66 ± 0.02
S2	δ Si	3.2	4	1.62	0.60 ± 0.02
S3	hom. Be	2.4	12	1.52	0.62 ± 0.03

TABLE I: Sample characteristics: Type of extra doping, electron density n_e and mobility μ_e of the 2DES, the critical point ν_c [29], and the width scaling exponent κ for the $\nu = 1 \rightarrow 2$ transition.

order of unity. With this direct access to $\xi \propto 1/T_0$ it is possible to test for scaling behavior of ξ at the edges of the plateau as long as we are careful enough to stay within the localized regime.

Earlier experiments confirmed the expected temperature dependence of $\sigma_{xx}(T)$ and extracted ξ in the QHE-regime [26, 27], but either did not analyze the scaling behavior or were restricted to a small filling factor range close to the quasi-metallic regime. In a recent experiment on the QH plateau-insulator transition VRH conductivity following Eq. 1 was also established to that regime and was used to determine ξ , finding a rough agreement with the prediction of universal scaling [28].

In this paper we show that when analyzing the conductivity deep into the localized regime of the quantum Hall plateau transition we find a clear universal scaling behavior of the localization length $\xi \propto |\delta\nu|^{-\gamma}$ as function of the filling factor distance $\delta\nu = \nu - \nu_c$ to the critical point at ν_c with a universal $\gamma = 2.3$. Such a universality is even observed in samples where non-universal exponents extracted from temperature dependent peak-width scaling are found. Going even further, we show that the conductivities $\sigma_{xx}(T, \delta\nu)$ in the VRH regime for $\delta\nu < 0.3$ can be scaled to a single parameter function of $|\delta\nu|^\gamma/T$ as predicted by scaling theory for the critical regime.

The samples used in this work are based on modulation doped GaAs/AlGaAs heterostructures with additional scatterers in the active region of the 2DES [30]. The scatterers are provided by doping the GaAs close to the heterojunction with Si or Be, either as a δ -layer or a weak homogeneous background. This results in relatively low mobilities of a few m^2/Vs (see table I). In order to allow a highly sensitive two-point measurement of very low conductivities the samples were patterned into Corbino geometry using contacts fabricated by standard Ni/Au/Ge alloy annealing. Here the conductivity is given by $\sigma_{xx} = (I/2\pi V) \ln(r_2/r_1)$ where $r_1 = 500 \mu\text{m}$ and $r_2 = 550 \mu\text{m}$ are the inner and the outer radius of the Corbino disk. The samples were mounted onto the cold finger of a dilution refrigerator with base temperature below 20 mK and positioned into the center of a superconducting solenoid.

The sample conductivity $\sigma_{xx}(B, T)$ as a function of magnetic field B and temperature T was extracted from individually measured I - V characteristics by numerical differentiation in the linear regime close to zero bias. For

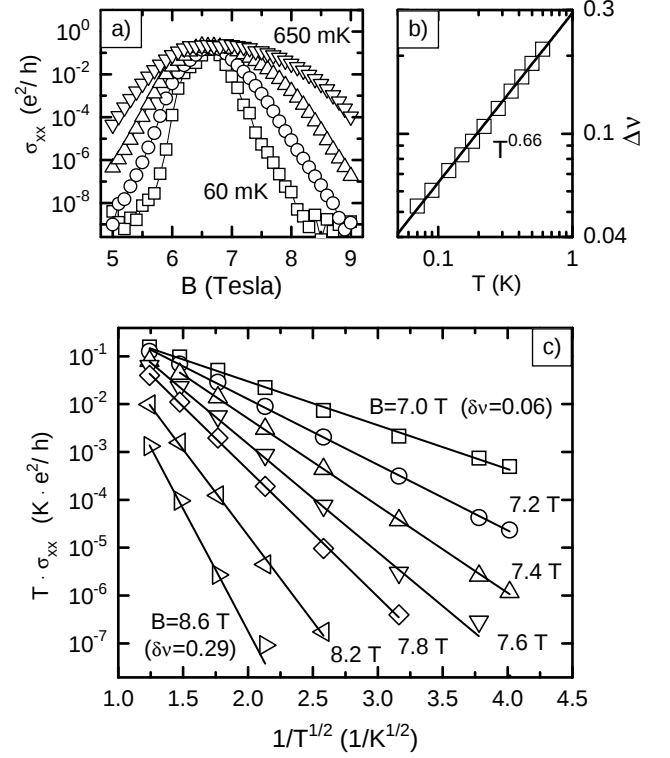


FIG. 1: a) Conductivity σ_{xx} of sample S1 at different temperatures for the transition between plateaus $\nu = 2$ and $\nu = 1$. b) Full width at half maximum $\Delta\nu$ of the conductivity peak fitted by a power law $\Delta\nu \propto T^\kappa$. c) Variable-range hopping fit of σ_{xx} to Eq. 1 with prefactor $\sigma_0 \propto 1/T$. The axes are rescaled to show straight line for the prediction of Eq. 1.

each curve we identified the linear regime which ranged from a few μV around the QHE plateau transition at low temperatures up to a few mV in the plateau center. This method allowed us to measure the conductivity accurately in a huge range between $10^{-13} \Omega^{-1}$ in the plateau center up to $10^{-5} \Omega^{-1}$ in the maximum of the plateau transition.

In Fig. 1a $\sigma_{xx}(B, T)$ of sample S1 is shown for the transition between the QHE plateaus at $\nu = 1$ and $\nu = 2$. We concentrate our studies on this transition where the spin gap is sufficiently large to exclude activated transport. The critical point ν_c of this transition, listed in table I, is given by the position of the maximum in $\sigma_{xx}(\nu)$.

Before analyzing the VRH transport we tested the conventional scaling behavior of the plateau transition width. Data for the full-width at half maximum $\Delta\nu$ of the peak in σ_{xx} as a function of filling factor $\nu = \hbar n/eB$ are shown in Fig. 1b for sample S1. For all investigated samples $\Delta\nu$ follows a power-law behavior $\Delta\nu \propto T^\kappa$ down to temperatures below 60 mK. However, as already reported in earlier work on similar samples [15] the critical exponents κ as presented in table I considerably deviate from the proposed universal value $\kappa = 0.43$ [6].

Let us now turn to a closer analysis of the VRH regime.

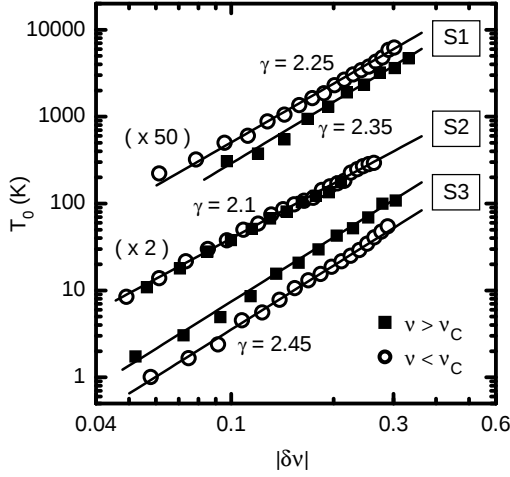


FIG. 2: Characteristic temperature T_0 as function of the distance $|\delta\nu|$ to the critical point for both sides of the $\nu = 1 \rightarrow 2$ plateau transition on a logarithmic scale. The data for different samples S1, S2 and S3 are shifted for clarity. The lines show power-law fits $T_0 \propto |\delta\nu|^\gamma$. Within the 2σ -confidence interval of ± 0.2 the extracted exponents agree with the expected $\gamma = 2.3$.

As shown in Fig. 1c for sample S1 the data fit well the predicted temperature behavior of Eq. 1 with a prefactor $\sigma_0 \propto 1/T$. We also tested for activated behavior, Coulomb gap with constant σ_0 , and Mott hopping $\sigma_{xx} \propto T^{-m} \exp((T_0/T)^{1/3})$ for various m , all matching our data worse. From these fits to Eq. 1 we are able to extract the characteristic temperature T_0 in the VRH regime. To stay well inside this localized regime we only take into account filling factors where the low temperature conductivity is at least two orders of magnitude below the critical conductivity σ_c .

In Fig. 2 the characteristic temperature T_0 is plotted against the distance $|\delta\nu| = |\nu - \nu_c|$ to the critical point ν_c . The data follows a power-law behavior $T_0 \propto |\delta\nu|^\gamma$ up to distances as large as $|\delta\nu| \approx 0.3$. This demonstrates that the localization length $\xi \propto 1/T_0$ follows a scaling behavior deep into the localized regime.

The most interesting result is that we find an accurate universal scaling of the localization length ξ with temperature. Our extracted values for γ agree within experimental accuracy well with the numerical results $\gamma = 2.3$ ([1] and references therein) as well as with the exponents determined from size dependent scaling experiments [5]. This underlines the fact that our direct scaling analysis in the VRH regime suits much better as an access to the localization length and its scaling behavior than temperature dependent peak-width scaling where no universality is observed. In fact, for such a conventional analysis we are still lacking a sufficient knowledge of the temperature dependent transport mechanisms in the metallic regime of the QHE plateau transition.

Until now we used the term scaling in a rather reduced

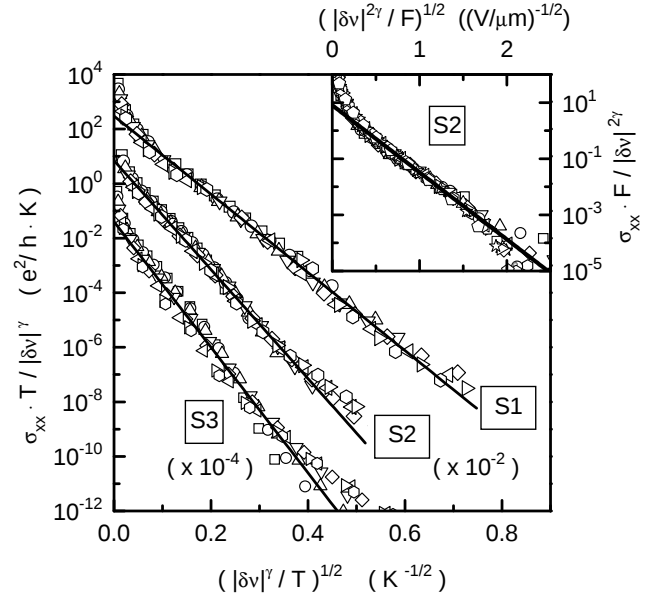


FIG. 3: Rescaling of the conductivity $\sigma_{xx}(T, \nu)$, presented for sample S1 in figure 1c), as function of a single parameter $x = |\delta\nu|^\gamma/T$ for $\nu > \nu_c$ ($T = 60 \dots 700$ mK, $|\delta\nu| < 0.3$). Inset: Test of scaling with a single parameter $y = |\delta\nu|^{2\gamma}/F$ for the dependence on electric field ($F = 2 \dots 200$ V/m, $\sigma_{xx} \geq 10^{-4} e^2/h$).

sense as synonym for a power-law behavior of the localization length ξ . Of course scaling includes much more, namely the existence of a single parameter scaling function $\sigma_{xx} = f(x)$ with a parameter $x(T, \delta\nu)$. Using our above results in the VRH regime an appropriate definition is $x = |\delta\nu|^\gamma/T \propto T_0/T$ with the above deduced exponents γ . The postulation of single parameter scaling together with the finding of $\sigma_0 \propto 1/T$ then fixes the prefactor in Eq. 1 to $\sigma_0(\delta\nu, T) = \sigma^* |\delta\nu|^\gamma/T$ with a constant σ^* . This yields a scaling of the conductivity in the form

$$\sigma_{xx} \left(\frac{|\delta\nu|^\gamma}{T} \right) = \sigma^* \frac{|\delta\nu|^\gamma}{T} \exp \left(-\sqrt{T^* \frac{|\delta\nu|^\gamma}{T}} \right) \quad (2)$$

where T^* is constant.

In Fig. 3 we have plotted all the conductivity data $\sigma_{xx}(\nu, T)$ for $\nu > \nu_c$ as function of a single parameter $|\delta\nu|^\gamma/T$. The values for γ are taken from the power-law fits of T_0 as shown in Fig. 2. Rescaling the axes in a proper way indeed shows that all experimental points fall onto straight lines as represented by the scaling function in Eq. 2. Therefore, the conductivity in the VRH regime for $\delta\nu < 0.3$ and $\nu > \nu_c$ follows the stringent postulation of single parameter scaling and thus demonstrates the large validity range of the universal scaling phenomenon in the transition between QHE plateaus.

For $\nu < \nu_c$, i.e. approaching the spin gap induced plateau at $\nu = 1$, the single parameter rescaling does not look as good as for approaching the Landau gap at $\nu = 2$, although Fig. 2 showed the same quality of T_0 -scaling for

both sides of the transition. This discrepancy probably mirrors a more complicated behavior of the prefactor σ_0 in Eq. 1. Obviously it can no more be written as a simple function $|\delta\nu|^\gamma/T \propto T_0/T$. Such a more complicated behavior in this regime is no surprise taking into account the redistribution of electrons between spin states and the emerging of spin textures as a function of ν at this filling range [31].

In addition to the temperature dependence of σ_{xx} in the VRH regime we have also investigated its dependence on the electric field strength F . In the nonlinear regime at high voltages the effect of F can be interpreted as an effective temperature $T_F = eF\xi/2k_B$ [22]. Using Eq. 1 the conductivity is then rewritten to $\sigma_{xx} = \sigma_0^F(F) \exp\left(-\sqrt{F_0/F}\right)$ with $F_0 \propto T_0/\xi \propto 1/\xi^2$. Analogous to the single parameter scaling with temperature in the VRH regime the natural reduced parameter for scaling with electric field is defined by $y(F, \nu) = |\delta\nu|^{2\gamma}/F$. Applying such an analysis to our data without any additional fit parameter (i.e. using the exponents γ as determined from $T_0(\nu)$, see Fig. 2) we find for $\nu > \nu_c$ for all data in the range $\sigma_{xx} \geq 10^{-4}e^2/h$ a single parameter scaling; an example for sample S2 is shown in the inset of figure 3.

In conclusion we have investigated the temperature and electric field dependence of the conductivity in the QHE plateau transition for samples where no universal behavior is found in the conventional temperature dependent peak-width scaling experiments. We find a revival of universality in the VRH regime where the localization length ξ scales as $\xi \propto |\delta\nu|^{-\gamma}$ with an experimentally deduced scaling exponent close to the theoretically expected value $\gamma = 2.3$. Even further, we have shown that all the data on the Landau gap side of the transition can be rescaled on a single parameter function over more than five orders of magnitude in the conductivity.

We thank F. Evers, B. Huckestein, B. Kramer and D. G. Polyakov for stimulating discussions. The samples were grown by K. Ploog at the Max Planck-Institut für Festkörperforschung.

* Electronic address: hohls@nano.uni-hannover.de

- [1] B. Huckestein, Rev. Mod. Phys. **67**(2), 357 (1995).
- [2] S. L. Sondhi, S. M. Girvin, J. P. Carini, and D. Shahar, Rev. Mod. Phys. **69**(1), 315 (1997).
- [3] A. M. M. P. Pruisken, Phys. Rev. Lett. **61**(11), 1297 (1988).
- [4] B. Huckestein and B. Kramer, Phys. Rev. Lett. **64**(12), 1437 (1990).
- [5] S. Koch, R. J. Haug, K. v. Klitzing, and K. Ploog, Phys. Rev. Lett. **67**(7), 883 (1991).
- [6] H. P. Wei, D. C. Tsui, M. A. Paalanen, and A. M. M. P. Pruisken, Phys. Rev. Lett. **61**(11), 1294 (1988).
- [7] E. Chow, H. P. Wei, S. M. Girvin, and M. Shayegan, Phys. Rev. Lett. **77**(6), 1143 (1996).
- [8] L. W. Engel, D. Shahar, C. Kurdak, and D. C. Tsui, Phys. Rev. Lett. **71**(16), 2638 (1993).
- [9] D. Shahar, D. C. Tsui, M. Shayegan, R. N. Bhatt, and J. E. Cunningham, Phys. Rev. Lett. **74**(22), 4511 (1995).
- [10] D. Shahar, D. C. Tsui, M. Shayegan, E. Shimshoni, and S. L. Sondhi, Science **274**, 589 (1996).
- [11] M. Hilke, D. Shahar, S. H. Song, D. C. Tsui, Y. H. Xie, and D. Monroe, Nature **395**, 675 (1998).
- [12] D. Shahar, D. C. Tsui, M. Shayegan, E. Shimshoni, and S. L. Sondhi, Phys. Rev. Lett. **79**(3), 479 (1997).
- [13] W. Pan, D. Shahar, D. C. Tsui, H. P. Wei, and M. Razeghi, Phys. Rev. B **55**(23), 15431 (1997).
- [14] R. T. F. van Schaijk, A. de Visser, S. Olsthoorn, H. P. Wei, and A. M. M. P. Pruisken, Phys. Rev. Lett. **84**, 1567 (2000).
- [15] S. Koch, R. J. Haug, K. v. Klitzing, and K. Ploog, Phys. Rev. B **43**(8), 6828 (1991).
- [16] E. Chow and H. P. Wei, Phys. Rev. B **52**(19), 13749 (1995).
- [17] F. Hohls, U. Zeitler, R. J. Haug, and K. Pierz, Physica B **298**(1-4), 88 (2001).
- [18] D. Shahar, M. Hilke, C. C. Li, D. C. Tsui, S. L. Sondhi, and M. Razeghi, Solid State Commun. **107**(1), 19 (1998).
- [19] N. Q. Balaban, U. Meirav, and I. Bar-Joseph, Phys. Rev. Lett. **81**(22), 4967 (1998).
- [20] P. T. Coleridge, Phys. Rev. B **60**(7), 4493 (1999).
- [21] E. Shimshoni, Phys. Rev. B **60**(15), 10691 (1999).
- [22] D. G. Polyakov and B. I. Shklovskii, Phys. Rev. B **48**(15), 11167 (1993); Phys. Rev. Lett. **70**(24), 3796 (1993).
- [23] F. Hohls, U. Zeitler, and R. J. Haug, Phys. Rev. Lett. **86**(122), 5124 (2001).
- [24] G. Ebert, K. von Klitzing, C. Probst, E. Schubert, K. Ploog, and G. Weimann, Solid State Commun. **45**, 625 (1983).
- [25] A. Briggs, Y. Guldner, J. P. Vieren, M. Voos, J. P. Hirtz, and M. Razeghi, Phys. Rev. B **27**, 6549 (1983).
- [26] S. Koch, R. J. Haug, K. v. Klitzing, and K. Ploog, Semicond. Sci. Technol. **10**, 209 (1995).
- [27] M. Furlan, Phys. Rev. B **57**(23), 14818 (1998).
- [28] S. Q. Murphy, J. L. Hicks, W. K. Liu, S. J. Chung, K. J. Goldammer, and M. B. Santos, Physica E **6**, 293 (2000).
- [29] Due to strong δ -doping with Be resp. Si the density of states becomes asymmetric and the critical filling factor is shifted from the ideal $\nu_c = 1.5$ to lower resp. higher filling factors, R. J. Haug, R. R. Gerhardts, K. v. Klitzing, and K. Ploog, Phys. Rev. Lett. **59**(12), 1349 (1987).
- [30] K. Ploog, J. Cryst. Growth. **81**, 304 (1987).
- [31] S. M. Girvin and A. H. MacDonald, in *Perspectives in Quantum Hall Effects*, edited by S. Das Sarma and A. Pinczuk (Wiley, New York, 1997).